

TS5A22362 具有负信号功能的 0.65Ω 双通道 SPDT 模拟开关

1 特性

- 指定的先断后合开关
- 负信号处理功能：最大摆幅为从 -2.75V 至 2.75V ($V_{CC} = 2.75\text{V}$)
- 低导通电阻（典型值 0.65Ω ）
- 低电荷注入
- 出色的导通状态电阻匹配
- 2.3V 至 5.5V 电源 (V_{CC})
- 闩锁性能超过 100mA ，符合 JESD 78 II 类规范
- 静电放电 (ESD) 性能测试符合 JESD 22 标准
 - 2500V 人体放电模式 (A114-B, II 类)
 - 1500V 充电器件模型 (C101)
 - 200V 机器模型 (A115-A)

2 应用

- 手机
- 个人数字助理 (PDA)
- 便携式仪表
- 音频路由
- 医疗成像

3 说明

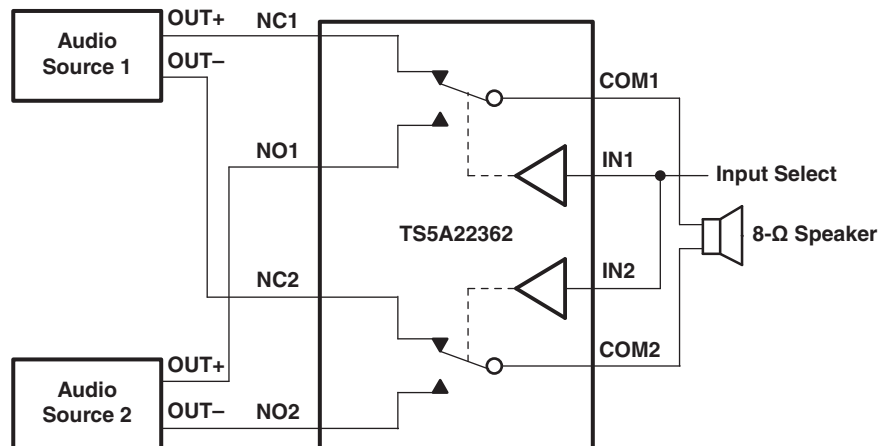
TS5A22362 是一款双向、双通道单刀双掷 (SPDT) 模拟开关，工作电压范围为 2.3V 至 5.5V 。该器件支持负信号摆幅，允许低于接地电平的信号通过开关，同时不发生失真。先断后合特性可防止信号在跨路径传输时出现失真。该器件同时拥有低导通电阻、出色的通道间导通状态电阻匹配以及最小总谐波失真 (THD) 性能，是音频应用的理想选择。该器件还针对医疗成像应用提供了一种非磁性封装，即 $3.00\text{mm} \times 3.00\text{mm}$ DRC 封装。

器件信息⁽¹⁾

器件型号	封装	封装尺寸（标称值）
TS5A22362	VSON (10)	$3.00\text{mm} \times 3.00\text{mm}$
	DSBGA (10)	$1.86\text{mm} \times 1.36\text{mm}$
	VSSOP (10)	$3.00\text{mm} \times 3.00\text{mm}$

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

典型应用原理图



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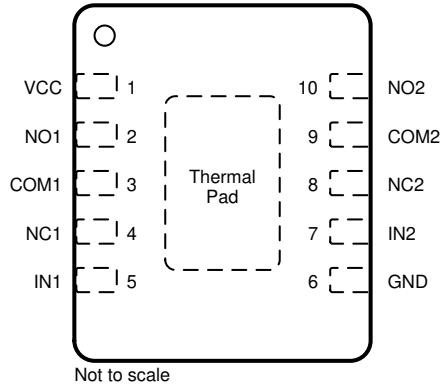
4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision D (March 2018) to Revision E	Page
• Changed the YZP Package view From: Top View To: Bottom View	3
Changes from Revision C (June 2017) to Revision D	Page
• Changed the YZP Package From: Laser Marketing View and Bump View To: Top View	3
• Changed the Q_C TYP value From: 10 pC To: 150 pC in the <i>Electrical Characteristics for 5-V Supply</i> table	8
Changes from Revision B (September 2015) to Revision C	Page
• Changed the V_{IN} MAX value From: V_{CC} To: 5.5 V in the <i>Recommended Operating Conditions</i> table	4
Changes from Revision A (August 2015) to Revision B	Page
• Changed C_L TEST CONDITION value for all THD PARAMETERS from 15 pf to 35 pf.	6
Changes from Original (June 2015) to Revision A	Page
• Changed the Functional Block Diagram.	15

5 Pin Configuration and Functions

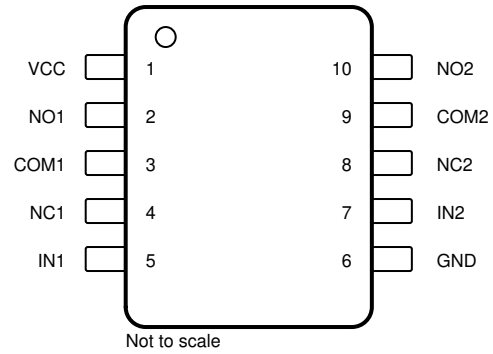
**DRC Package
10-Pin VSON
Top View**



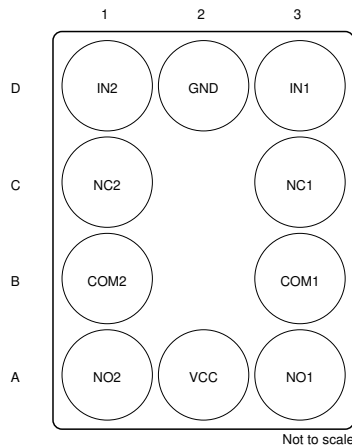
The exposed center pad, if used, must be

connected as a secondary GND or left electrically open.

**DGS Package
10-Pin VSSOP
Top View**



**YZP Package
10-Pin DSBGA
Bottom View**



Pin Functions

PIN				TYPE	DESCRIPTION
NAME	VSON	VSSOP	DSBGA		
VCC	1	1	A2	—	Power Supply
NO1	2	2	A3	I/O	Normally Open (NO) signal path, Switch 1
COM1	3	3	B3	I/O	Common signal path, Switch 1
NC1	4	4	C3	I/O	Normally Closed (NC) signal path, Switch 1
IN1	5	5	D3	I	Digital control pin , Switch 1
GND	6	6	D2	—	Ground
IN2	7	7	D1	I	Digital control pin, Switch 2
NC2	8	8	C1	I/O	Normally Closed (NC) signal path, Switch 2
COM2	9	9	B1	I/O	Common signal path, Switch 2
NO2	10	10	A1	I/O	Normally Open (NO) signal Path, Switch 2

6 Specifications

6.1 Absolute Maximum Ratings

 over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

			MIN	MAX	UNIT
V _{CC} ⁽²⁾		Supply voltage ⁽³⁾	−0.5	6	V
V _{NC} V _{NO} V _{COM}		Analog voltage ⁽³⁾ ⁽⁴⁾ ⁽⁵⁾	V _{CC} − 6	V _{CC} + 0.5	V
I _{I/OK}	Analog port diode current	V _{NC} , V _{NO} , V _{COM} < 0 or V _{NC} , V _{NO} , V _{COM} > V _{CC}	−50	50	mA
I _{NC} I _{NO} I _{COM}	ON-state switch current	V _{NC} , V _{NO} , V _{COM} = 0 to V _{CC}	−150	150	mA
	ON-state peak switch current ⁽⁶⁾		−300	300	
I _{NC} ⁽³⁾ ⁽⁷⁾ ⁽⁸⁾ I _{NO} ⁽³⁾ ⁽⁷⁾ ⁽⁸⁾ I _{COM} ⁽³⁾ ⁽⁷⁾ ⁽⁸⁾	ON-state switch current	V _{NC} , V _{NO} , V _{COM} = 0 to V _{CC}	−350	350	mA
	ON-state peak switch current ⁽⁶⁾		−500	500	
V _I		Digital input voltage	−0.5	6.5	V
I _{IK}	Digital input clamp current ⁽³⁾ ⁽⁴⁾	V _I < 0	−50	50	mA
I _{CC} I _{GND}		Continuous current through V _{CC} or GND	−100	100	mA
T _{std}		Storage temperature	−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
- (3) All voltages are with respect to ground, unless otherwise specified.
- (4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (5) This value is limited to 5.5 V maximum.
- (6) Pulse at 1-ms duration < 10% duty cycle.
- (7) $V_{CC} = 3.0$ V to 5.0 V, $T_A = -40^\circ\text{C}$ to 85°C .
- (8) For YZP package only.

6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$ Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2500	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_{CC}	Supply voltage	2.3	5.5	V
V_{NC} V_{NO} V_{COM}	Signal path voltage	$V_{CC} - 5.5$	V_{CC}	V
V_{IN}	Digital control	GND	5.5	V

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TS5A22362			UNIT
		DGS (VSSOP)	DRC (VSON)	YZP (DSBGA)	
		10 PINS	10 PINS	10 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	163.3	44.3	90.9	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	56.4	70.1	0.3	°C/W
R _{θJB}	Junction-to-board thermal resistance	83.1	19.3	8.3	°C/W
ψ _{JT}	Junction-to-top characterization parameter	6.8	2.0	3.2	°C/W
ψ _{JB}	Junction-to-board characterization parameter	81.8	19.4	8.3	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics for 2.5-V Supply

V_{CC} = 2.3 V to 2.7 V, T_A = –40°C to 85°C (unless otherwise noted) ⁽¹⁾

PARAMETER	TEST CONDITIONS	T _A	V _{CC}	MIN	TYP	MAX	UNIT
Analog Switch							
V _{COM} , V _{NO} , V _{NC}	Analog signal range			V _{CC} – 5.5		V _{CC}	V
R _{on}	ON-state resistance	V _{NC} or V _{NO} = V _{CC} , 1.5 V, V _{CC} – 5.5 V I _{COM} = –100 mA, COM to NO or NC, see Figure 13	25°C Full	2.7 V	0.65 1.3	0.94	Ω
ΔR _{on}	ON-state resistance match between channels	V _{NC} or V _{NO} = 1.5 V, I _{COM} = –100 mA, COM to NO or NC, see Figure 13	25°C Full	2.7 V	0.023 0.15	0.11	Ω
R _{on(flat)}	ON-state resistance flatness	V _{NC} or V _{NO} = V _{CC} , 1.5 V, V _{CC} – 5.5 V I _{COM} = –100 mA, COM to NO or NC, see Figure 13	25°C Full	2.7 V	0.18 0.5	0.46	Ω
I _{NC(OFF)} , I _{NO(OFF)}	NC, NO OFF leakage current	V _{NC} = 2.25 V, V _{CC} – 5.5 V V _{COM} = V _{CC} – 5.5 V, 2.25 V V _{NO} = Open COM to NO or V _{NO} = 2.25 V, V _{CC} – 5.5 V, V _{COM} = V _{CC} – 5.5 V, 2.25 V V _{NC} = Open COM to NC See Figure 14	25°C Full	2.7 V	–50 –375	50 375	nA
I _{COM(ON)}	COM ON leakage current	V _{NC} and V _{NO} = Floating, V _{COM} = V _{CC} , V _{CC} – 5.5 V See Figure 15	25°C Full	2.7 V	–50 –375	50 375	nA
Digital Control Inputs (IN) ⁽²⁾							
V _{IH}	Input logic high		Full		1.4	5.5	V
V _{IL}	Input logic low					0.6	
I _{IH} , I _{IL}	Input leakage current	V _{IN} = V _{CC} or 0	25°C Full	2.7 V	–250 –250	250 250	nA
Dynamic							
t _{ON}	Turnon time	V _{COM} = V _{CC} , R _L = 300 Ω, C _L = 35 pF, see Figure 17	25°C Full	2.5 V 2.3 V to 2.7 V	44 120	80	ns
t _{OFF}	Turnoff time	V _{COM} = V _{CC} , R _L = 300 Ω, C _L = 35 pF, see Figure 17	25°C Full	2.5 V 2.3 V to 2.7 V	22 70	70	ns
t _{BBM}	Break-before-make time	See Figure 18	25°C	2.5 V	1	7	ns
Q _C	Charge injection	V _{GEN} = 0, R _{GEN} = 0, C _L = 1 nF, see Figure 22	25°C	2.5 V	150		pC
C _{NC(OFF)} , C _{NO(OFF)}	NC, NO OFF capacitance	V _{NC} or V _{NO} = V _{CC} or GND, See Figure 16	25°C	2.5 V	70		pF

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, [Implications of Slow or Floating CMOS Inputs](#), [SCBA004](#).

Electrical Characteristics for 2.5-V Supply (continued)

 $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$, $T_A = -40^\circ\text{C to } 85^\circ\text{C}$ (unless otherwise noted) ⁽¹⁾

PARAMETER	TEST CONDITIONS	T_A	V_{CC}	MIN	TYP	MAX	UNIT
$C_{COM(ON)}$	NC, NO, COM ON capacitance $V_{COM} = V_{CC}$ or GND, Switch ON, $f = 10 \text{ MHz}$ See Figure 16	25°C	2.5 V		370		pF
C_i	Digital input capacitance $V_i = V_{CC}$ or GND See Figure 16	25°C	2.5 V		2.6		pF
BW	Bandwidth $R_L = 50 \Omega$, -3 dB See Figure 18	25°C	2.5 V		17		MHz
O_{ISO}	OFF isolation $R_L = 50 \Omega$ $f = 100 \text{ kHz}$, see Figure 20	25°C	2.5 V		-66		dB
X_{TALK}	Crosstalk $R_L = 50 \Omega$ $f = 100 \text{ kHz}$, see Figure 21	25°C	2.5 V		-75		dB
THD	Total harmonic distortion $R_L = 600 \Omega$, $C_L = 35 \text{ pF}$ $f = 20 \text{ Hz to } 20 \text{ kHz}$, see Figure 23	25°C	2.5 V		0.01%		
Supply							
I_{CC}	Positive supply current V_{COM} and $V_{IN} = V_{CC}$ or GND, V_{NC} and $V_{NO} = \text{Floating}$	25°C	2.7 V		0.2	1.1	μA
		Full				1.3	
I_{CC}	Positive supply current $V_{COM} = V_{CC} - 5.5 \text{ V}$, $V_{IN} = V_{CC}$ or GND, V_{NC} and $V_{NO} = \text{Floating}$	Full	2.7 V			3.3	μA

6.6 Electrical Characteristics for 3.3-V Supply

 $V_{CC} = 3 \text{ V to } 3.6 \text{ V}$, $T_A = -40^\circ\text{C to } 85^\circ\text{C}$ (unless otherwise noted) ⁽¹⁾

PARAMETER		TEST CONDITIONS		T _A	V _{CC}	MIN	TYP	MAX	UNIT
ANALOG SWITCH									
V _{COM} , V _{NO} , V _{NC}	Analog signal range					V _{CC} – 5.5		V _{CC}	V
R _{on}	ON-state resistance	V _{NC} or V _{NO} ≤ V _{CC} , 1.5 V, V _{CC} – 5.5 V, I _{COM} = –100 mA	COM to NO or NC, see Figure 13	25°C	3 V	0.61		0.87	Ω
				Full		0.97			
ΔR _{on}	ON-state resistance match between channels	V _{NC} or V _{NO} = 1.5 V, I _{COM} = –100 mA,	COM to NO or NC, see Figure 13	25°C	3 V	0.024		0.13	Ω
				Full		0.13			
R _{on(flat)}	ON-state resistance flatness	V _{NC} or V _{NO} ≤ V _{CC} , 1.5 V, V _{CC} – 5.5 V, I _{COM} = –100 mA	COM to NO or NC, see Figure 13	25°C	3 V	0.12		0.46	Ω
				Full		0.5			
I _{NC(OFF)} , I _{NO(OFF)}	NC, NO OFF leakage current	V _{NC} = 3 V, V _{CC} – 5.5 V V _{COM} = V _{CC} – 5.5 V, 3 V V _{NO} = Open COM to NO or V _{NO} = 3 V, V _{CC} – 5.5 V, V _{COM} = V _{CC} – 5.5 V, 3 V V _{NC} = Open COM to NC	See Figure 14	25°C	3.6 V	–50		50	nA
				Full		–375		375	
I _{COM(ON)}	COM ON leakage current	V _{NC} and V _{NO} = Floating, V _{COM} = V _{CC} , V _{CC} – 5.5 V	COM to NO or NC, see Figure 15	25°C	3.6 V	–50		50	nA
				Full		–375		375	
DIGITAL CONTROL INPUTS (IN) ⁽²⁾									
V _{IH}	Input logic high			Full		1.4		5.5	V
V _{IL}	Input logic low					0.8			
I _{IH} , I _{IL}	Input leakage current	V _{IN} = V _{CC} or 0	25°C	3.6 V	–250		250	nA	
			Full		–250		250		

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

Electrical Characteristics for 3.3-V Supply (continued)

 $V_{CC} = 3 \text{ V to } 3.6 \text{ V}$, $T_A = -40^\circ\text{C to } 85^\circ\text{C}$ (unless otherwise noted) ⁽¹⁾

PARAMETER		TEST CONDITIONS		T _A	V _{CC}	MIN	TYP	MAX	UNIT
DYNAMIC									
t _{ON}	Turnon time	V _{COM} = V _{CC} , R _L = 300 Ω	C _L = 35 pF, see Figure 17	25°C	3.3 V	34	80		ns
				Full	3 V to 3.6 V		120		
t _{OFF}	Turnoff time	V _{COM} = V _{CC} , R _L = 300 Ω	C _L = 35 pF, see Figure 17	25°C	3.3 V	19	70		ns
				Full	3 V to 3.6 V		70		
t _{BBM}	Break-before-make time	See Figure 18		25°C	3.3 V	1	7		ns
Q _C	Charge injection	V _{GEN} = 0, R _{GEN} = 0	C _L = 1 nF, see Figure 22	25°C	3.3 V	150			pC
C _{NC(OFF)} , C _{NO(OFF)}	NC, NO OFF capacitance	V _{NC} or V _{NO} = V _{CC} or V _{CC} – 5.5 V	See Figure 16	25°C	3.3 V	70			pF
C _{COM(ON)}	NC, NO, COM ON capacitance	V _{COM} = V _{CC} or GND, f = 10 MHz	See Figure 16	25°C	3.3 V	370			pF
C _I	Digital input capacitance	V _I = V _{CC} or GND	See Figure 16	25°C	3.3 V	2.6			pF
BW	Bandwidth	R _L = 50 Ω, –3 dB	Switch ON, see Figure 18	25°C	3.3 V	17.5			MHz
O _{ISO}	OFF isolation	R _L = 50 Ω	f = 100 kHz, see Figure 20	25°C	3.3 V	–68			dB
X _{TALK}	Crosstalk	R _L = 50 Ω	f = 100 kHz, see Figure 21	25°C	3.3 V	–76			dB
THD	Total harmonic distortion	R _L = 600 Ω, C _L = 35 pF	f = 20 Hz to 20 kHz, see Figure 23	25°C	3.3 V	0.008%			
SUPPLY									
I _{CC}	Positive supply current	V _{COM} and V _{IN} = V _{CC} or GND, V _{NC} and V _{NO} = Floating	25°C	3.6 V	0.1	1.2		μA	
			Full			1.3			
				V _{COM} = V _{CC} – 5.5 V, V _{IN} = V _{CC} or GND, V _{NC} and V _{NO} = Floating	Full	3.6 V		3.4	

6.7 Electrical Characteristics for 5-V Supply

 $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$, $T_A = -40^\circ\text{C to } 85^\circ\text{C}$ (unless otherwise noted) ⁽¹⁾

PARAMETER		TEST CONDITIONS		T _A	V _{CC}	MIN	TYP	MAX	UNIT
ANALOG SWITCH									
V _{COM} , V _{NO} , V _{NC}	Analog signal range					V _{CC} − 5.5		V _{CC}	V
R _{on}	ON-state resistance	V _{NC} or V _{NO} = V _{CC} , 1.6 V, V _{CC} = −5.5 V, I _{COM} = −100 mA	COM to NO or NC, see Figure 13	25°C	4.5 V	0.52	0.74		Ω
				Full		0.83			
ΔR _{on}	ON-state resistance match between channels	V _{NC} or V _{NO} = 1.6 V, I _{COM} = −100 mA	COM to NO or NC, see Figure 13	25°C	4.5 V	0.04	0.23		Ω
				Full		0.30			
R _{on(flat)}	ON-state resistance flatness	V _{NC} or V _{NO} = V _{CC} , 1.6 V, V _{CC} = −5.5 V, I _{COM} = −100 mA	COM to NO or NC, see Figure 13	25°C	4.5 V	0.076	0.46		Ω
				Full		0.5			
I _{NC(OFF)} , I _{NO(OFF)}	NC, NO OFF leakage current	V _{NC} = 4.5 V, V _{CC} − 5.5 V, V _{COM} = V _{CC} − 5.5 V, 4.5 V, V _{NO} = Open, COM to NO or V _{NO} = 4.5 V, V _{CC} − 5.5 V, V _{COM} = V _{CC} − 5.5 V, 4.5 V, V _{NC} = Open, COM to NC	See Figure 14	25°C	5.5 V	−50	50		nA
				Full		−375	375		
I _{COM(ON)}	COM ON leakage current	V _{NC} and V _{NO} = Floating, V _{COM} = V _{CC} , V _{CC} − 5.5 V	See Figure 15	25°C	5.5 V	−50	50		nA
				Full		−375	375		

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

Electrical Characteristics for 5-V Supply (continued)

 $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$, $T_A = -40^\circ\text{C to } 85^\circ\text{C}$ (unless otherwise noted) ⁽¹⁾

PARAMETER		TEST CONDITIONS		T _A	V _{CC}	MIN	TYP	MAX	UNIT
DIGITAL CONTROL INPUTS (IN) ⁽²⁾									
V _{IH}	Input logic high			Full		2.4		5.5	V
V _{IL}	Input logic low							0.8	
I _{IH} , I _{IL}	Input leakage current	V _{IN} = V _{CC} or 0	25°C	5.5 V		–250		250	nA
			Full			–250		250	
DYNAMIC									
t _{ON}	Turnon time	V _{COM} = V _{CC} , R _L = 300 Ω	C _L = 35 pF, see Figure 17	25°C	5 V		27	80	ns
				Full	4.5 V to 5.5 V			80	
t _{OFF}	Turnoff time	V _{COM} = V _{CC} , R _L = 300 Ω	C _L = 35 pF, see Figure 17	25°C	5 V		13	70	ns
				Full	4.5 V to 5.5 V			70	
t _{BBM}	Break-before-make time	V _{NC} = V _{NO} = V _{CC} /2 R _L = 300 Ω	C _L = 35 pF, see Figure 18	25°C	5 V	1	3.5		ns
Q _C	Charge injection	V _{GEN} = 0, R _{GEN} = 0	C _L = 1 nF, see Figure 22	25°C	5 V		150		pC
C _{NC(OFF)} , C _{NO(OFF)}	NC, NO OFF capacitance	V _{NC} or V _{NO} = V _{CC} or V _{CC} – 5.5 V	See Figure 16	25°C	5 V		70		pF
C _{COM(ON)}	NC, NO, COM ON capacitance	V _{COM} = V _{CC} or GND,	See Figure 16	25°C	5 V		370		pF
C _I	Digital input capacitance	V _I = V _{CC} or GND	See Figure 16	25°C	5 V		2.6		pF
BW	Bandwidth	R _L = 50 Ω	See Figure 18	25°C	5 V		18.3		MHz
O _{ISO}	OFF isolation	R _L = 50 Ω	f = 100 kHz, see Figure 20	25°C	5 V		–70		dB
X _{TALK}	Crosstalk	R _L = 50 Ω	f = 100 kHz, see Figure 21	25°C	5 V		–78		dB
THD	Total harmonic distortion	R _L = 600 Ω, C _L = 35 pF	f = 20 Hz to 20 kHz, see Figure 23	25°C	5 V		0.009%		
SUPPLY									
I _{CC}	Positive supply current	V _{COM} and V _{IN} = V _{CC} or GND, V _{NC} and V _{NO} = Floating	25°C	5.5 V		0.2	1.3	μA	
			Full				3.5		
		V _{COM} = V _{CC} – 5.5 V, V _{IN} = V _{CC} or GND, V _{NC} and V _{NO} = Floating	Full				5		

(2) All unused digital inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, [SCBA004](#).

6.8 Typical Characteristics

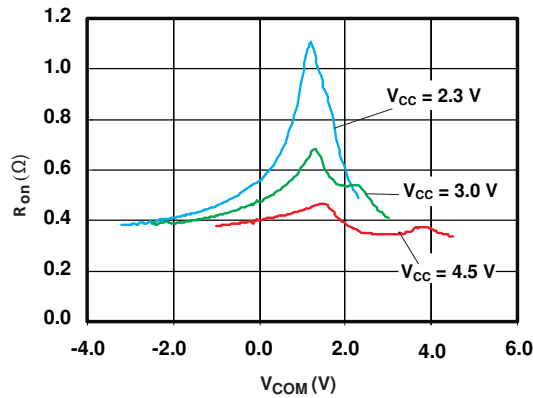


Figure 1. R_{on} vs V_{COM}

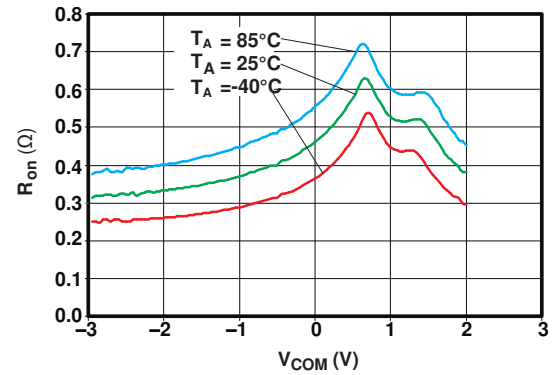


Figure 2. R_{on} vs V_{COM} ($V_{CC} = 2.7$ V)

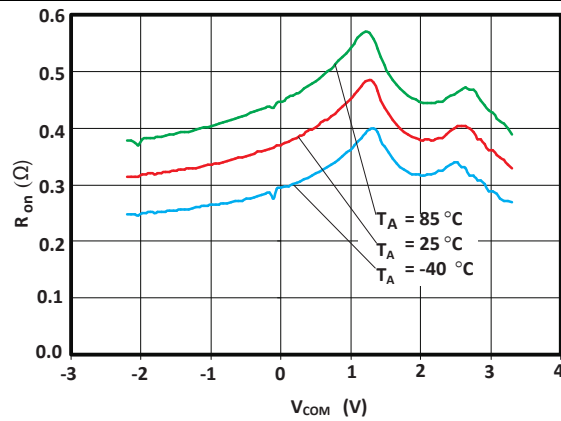


Figure 3. R_{on} vs V_{COM} ($V_{CC} = 3.3$ V)

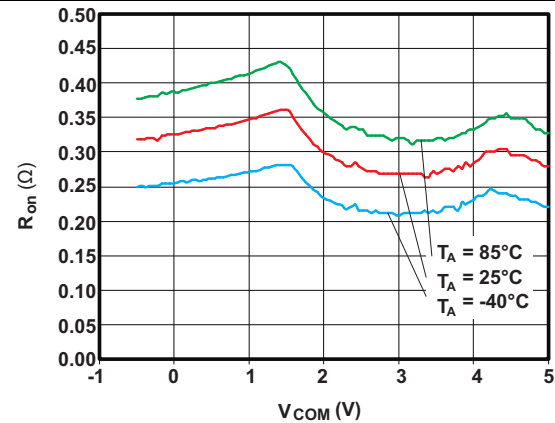


Figure 4. R_{on} vs V_{COM} ($V_{CC} = 5$ V)

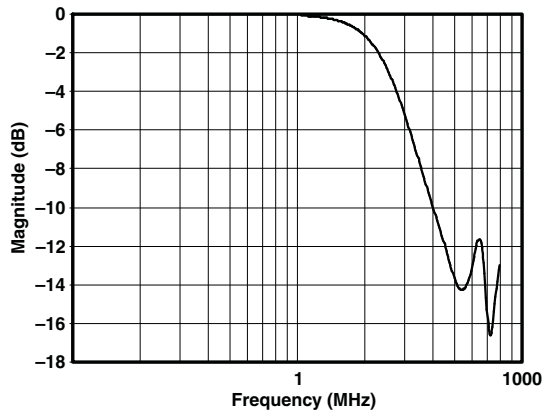


Figure 5. Insertion Loss

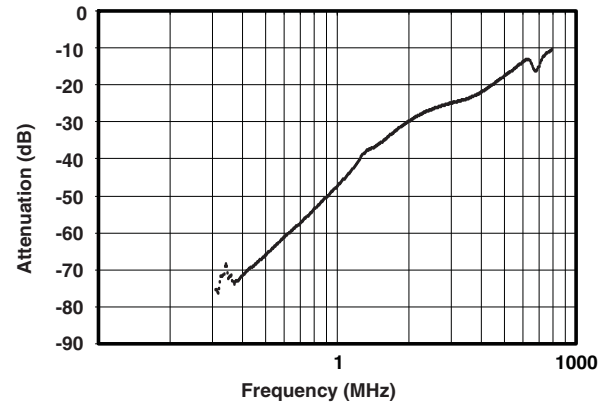


Figure 6. Off Isolation vs Frequency

Typical Characteristics (continued)

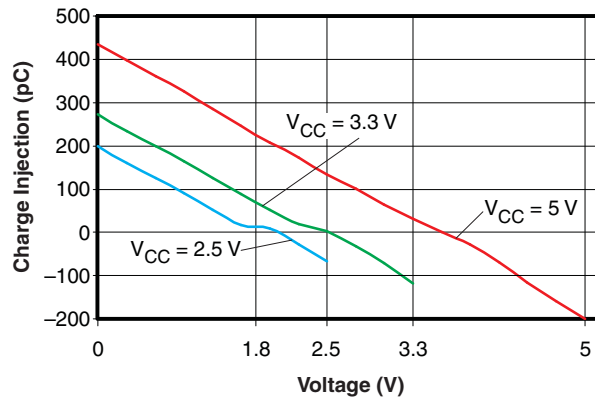


Figure 7. Charge Injection (Q_c) vs V_{COM}

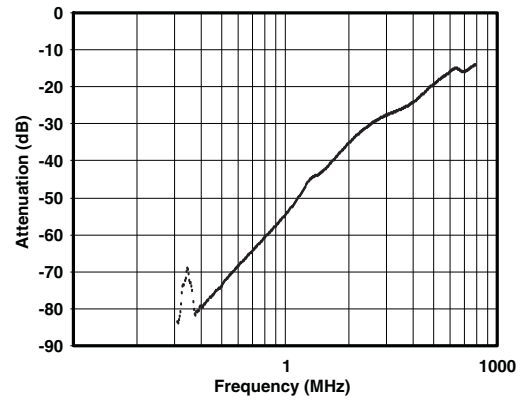


Figure 8. Crosstalk ($V_{CC} = 3.3\text{ V}$)

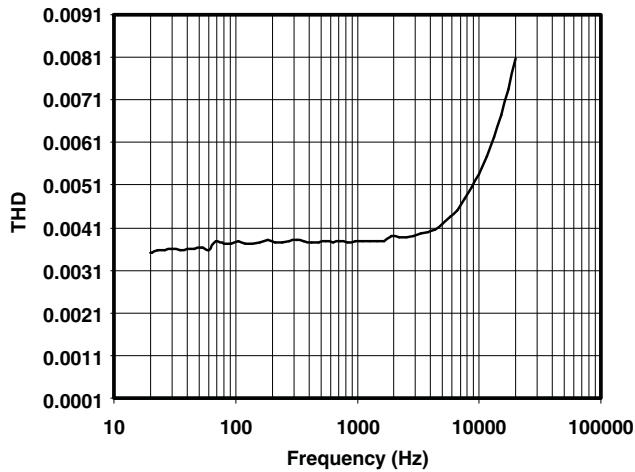


Figure 9. Total Harmonic Distortion vs Frequency

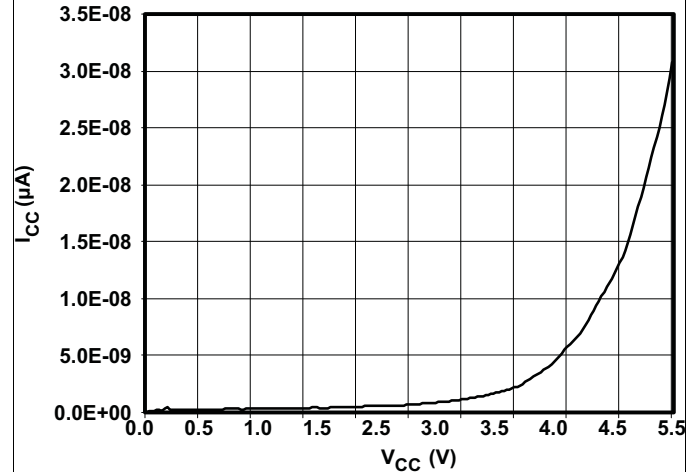


Figure 10. Power-Supply Current vs V_{CC}

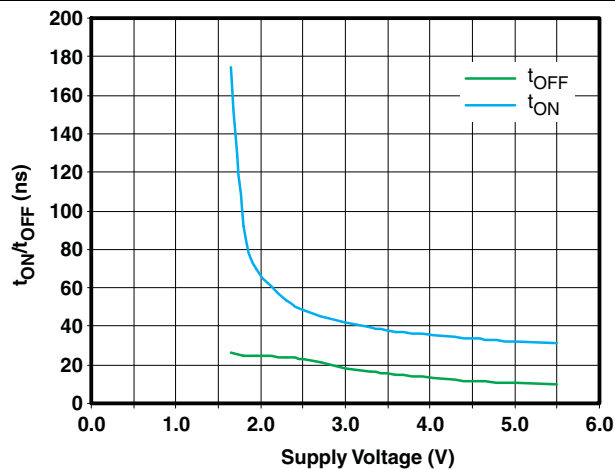


Figure 11. t_{ON} And t_{OFF} vs Supply Voltage

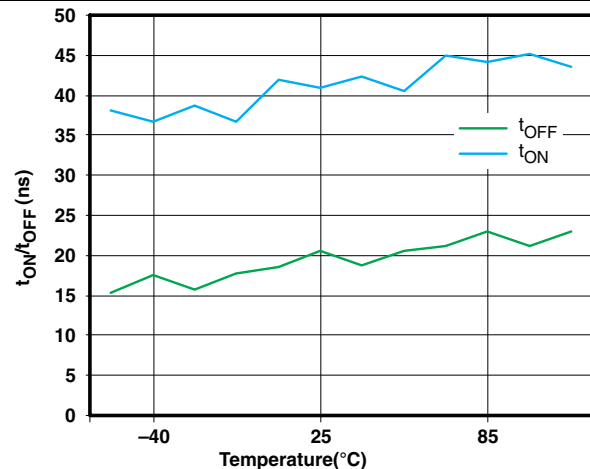


Figure 12. t_{ON} And t_{OFF} vs Temperature (2.5-V Supply)

7 Parameter Measurement Information

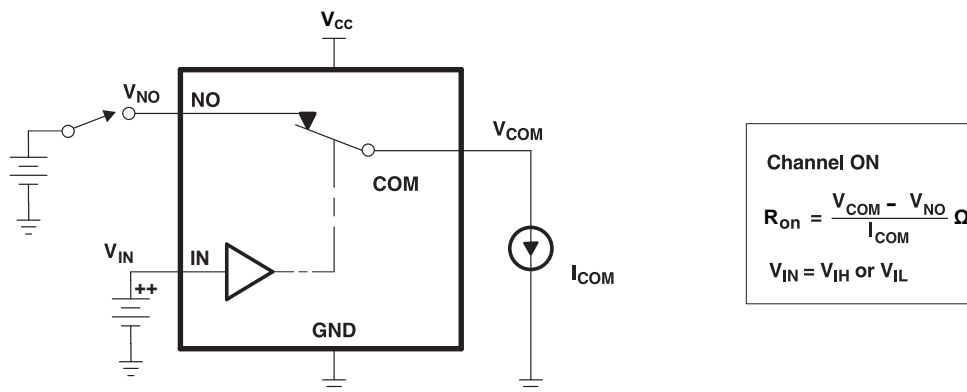


Figure 13. ON-state resistance (R_{on})

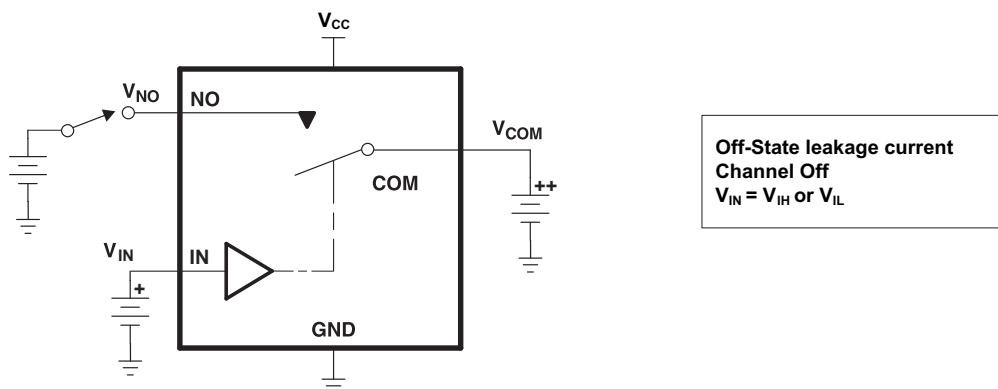
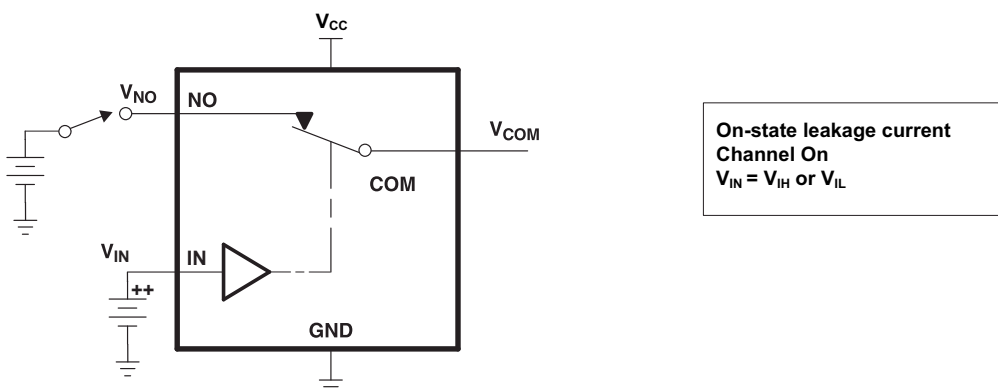


Figure 14. OFF-state leakage current ($I_{COM(OFF)}$, $I_{NO(OFF)}$)



**Figure 15. ON-state leakage current
($I_{COM(ON)}$, $I_{NO(ON)}$)**

Parameter Measurement Information (continued)

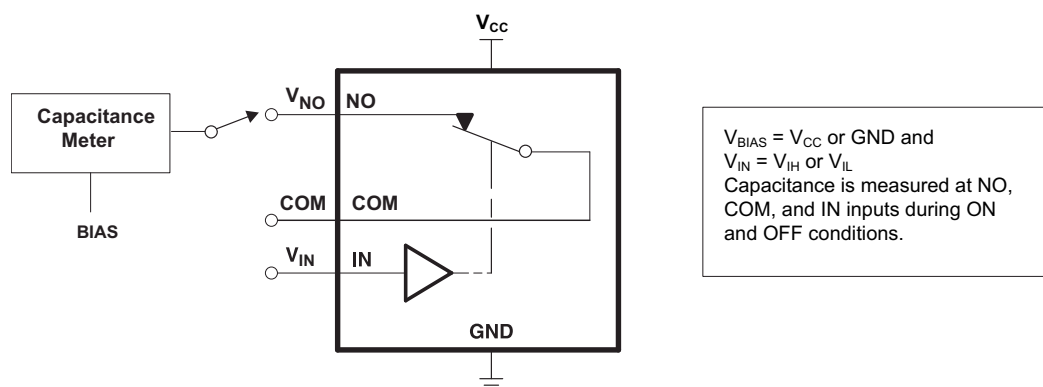
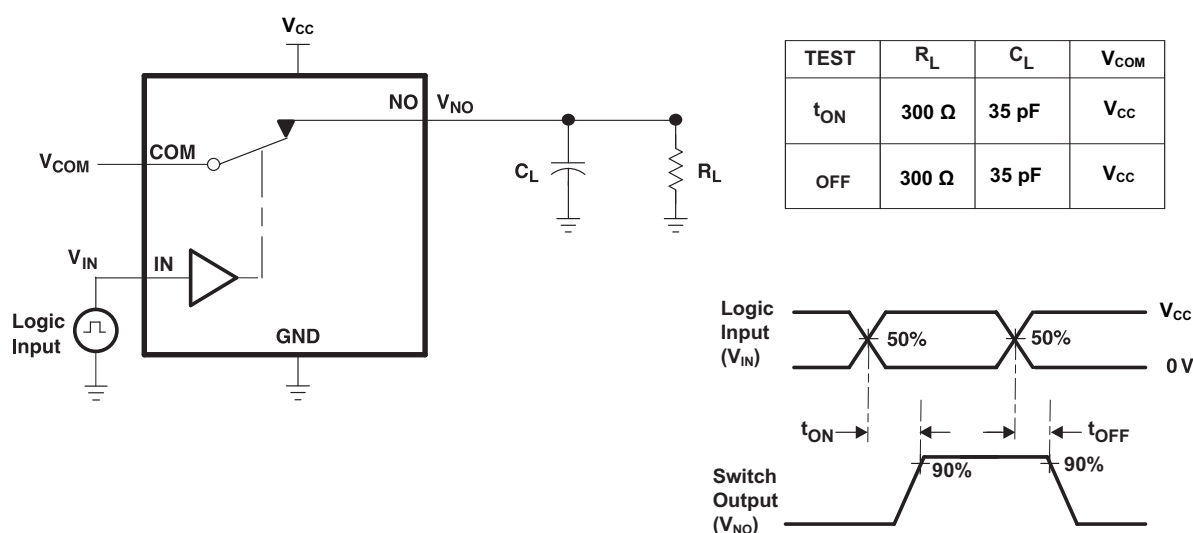


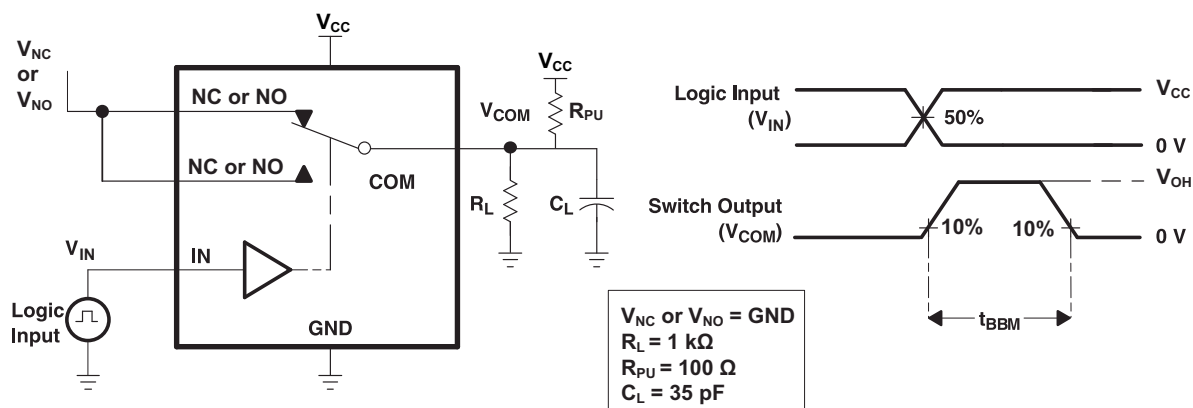
Figure 16. Capacitance
(C_I , $C_{COM(OFF)}$, $C_{COM(ON)}$, $C_{NO(OFF)}$, $C_{NO(ON)}$)



- A. All input pulses are supplied by generators having the following characteristics: PRR $\leq$ 10 MHz, $Z_O = 50 \Omega$, $t_r < 5$ ns, $t_f < 5$ ns.
- B. C_L includes probe and jig capacitance.

Figure 17. Turnon (t_{ON}) and Turnoff time (t_{OFF})

Parameter Measurement Information (continued)



- A. C_L includes probe and jig capacitance.
- B. All input pulses are supplied by generators having the following characteristics: PRR $\leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r < 5 \text{ ns}$, $t_f < 5 \text{ ns}$.

Figure 18. Break-Before-Make Time (t_{BBM})

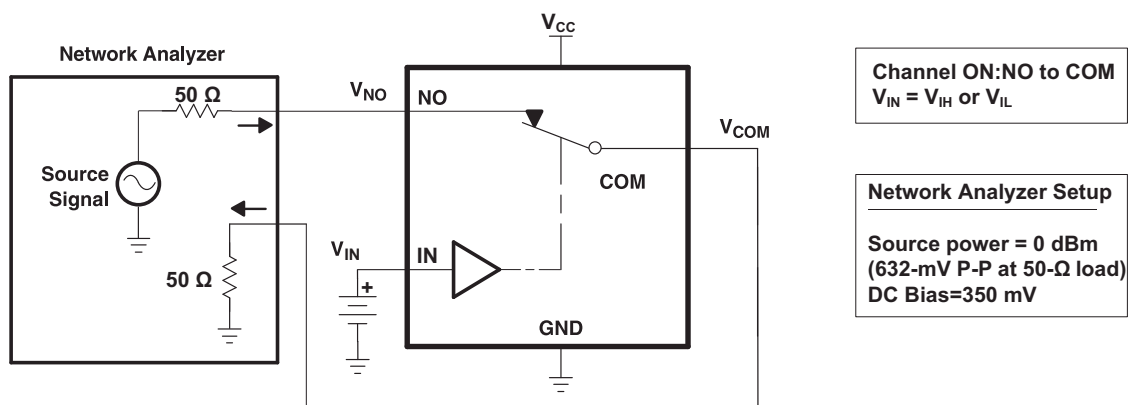


Figure 19. Bandwidth (BW)

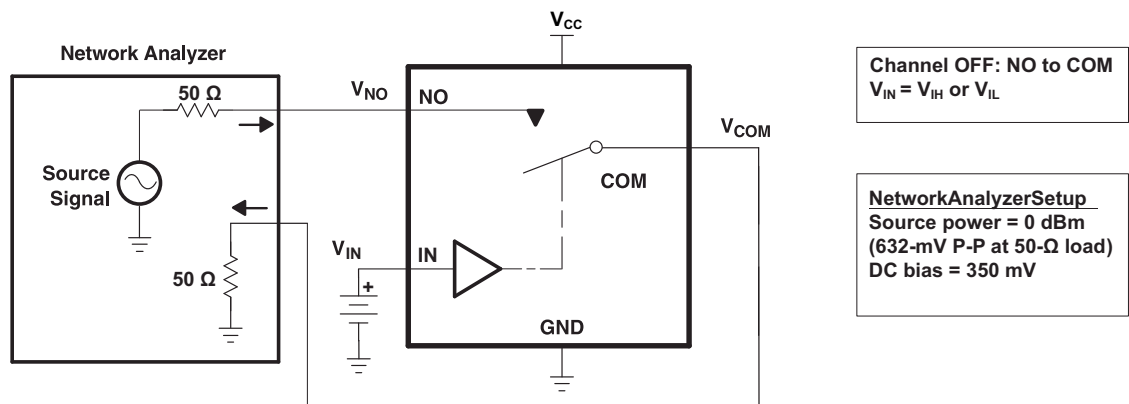


Figure 20. OFF isolation (O_{ISO})

Parameter Measurement Information (continued)

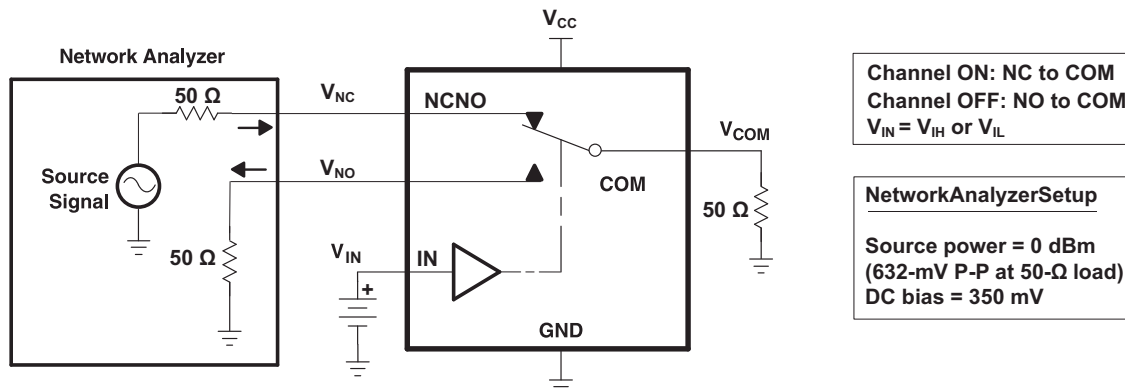
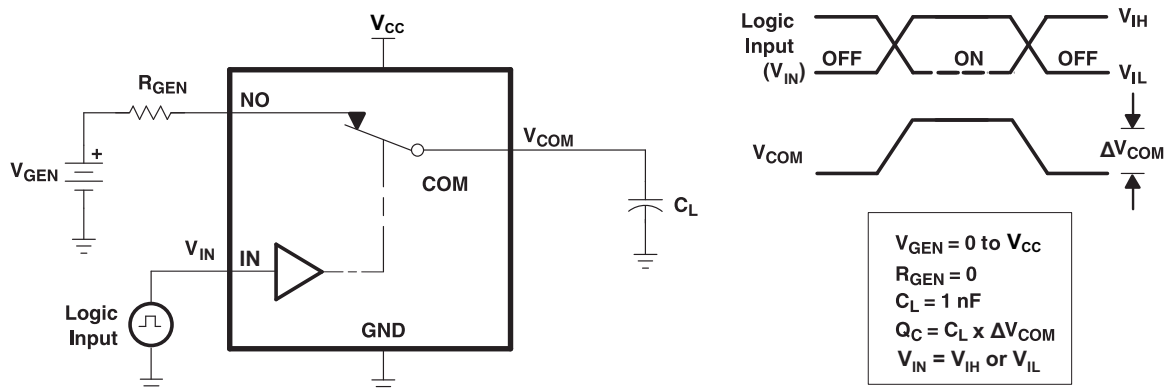


Figure 21. Crosstalk (X_{TALK})



- A. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r < 5 \text{ ns}$, $t_f < 5 \text{ ns}$.
- B. C_L includes probe and jig capacitance.

Figure 22. Charge injection (Q_C)

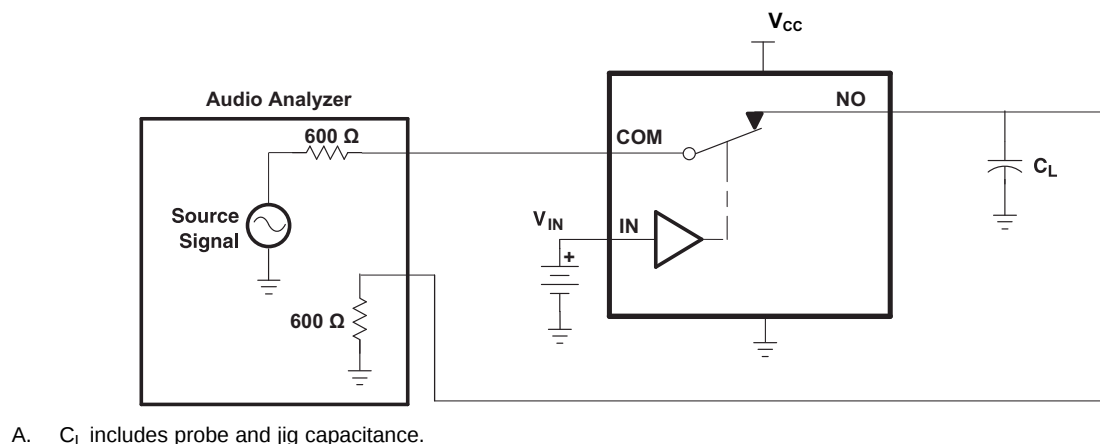
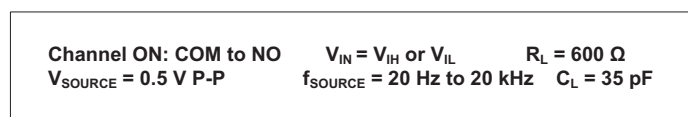


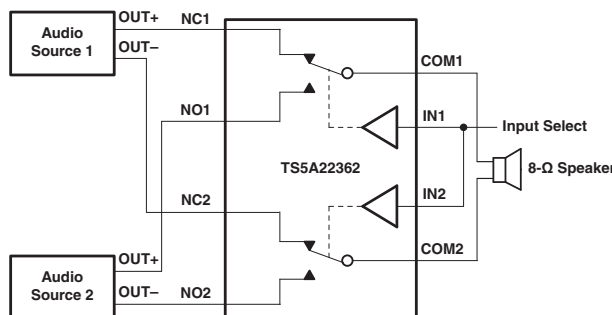
Figure 23. Total Harmonic Distortion (THD)

8 Detailed Description

8.1 Overview

The TS5A22362 is a bidirectional, 2-channel single-pole double-throw (SPDT) analog switches designed to operate from 2.3 V to 5.5 V. The devices feature negative signal capability that allows signals below ground to pass through the switch without distortion. The break-before-make feature prevents signal distortion during the transferring of a signal from one path to another. Low ON-state resistance, excellent channel-to-channel ON-state resistance matching, and minimal total harmonic distortion (THD) performance are ideal for audio applications.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Negative Signaling Capacity

The TS5A22362 dual SPDT switches feature negative signal capability that allows signals below ground to pass through without distortion. These analog switches operate from a single +2.3-V to +5.5-V supply. The input and output signal swing of the device is dependant of the supply voltage V_{CC} : the devices pass signals as high as V_{CC} and as low as $V_{CC} - 5.5$ V, including signals below ground with minimal distortion.

Table 1 shows the input/output signal swing the user can get with different supply voltages.

Table 1. Input/Output signal swing

SUPPLY VOLTAGE, V_{CC}	MINIMUM (V_{NC} , V_{NO} , V_{COM}) = $V_{CC} - 5.5$	MAXIMUM (V_{NC} , V_{NO} , V_{COM}) = V_{CC}
5.5 V	0 V	5.5 V
4.5 V	-1.9 V	4.5 V
3.6 V	-2.5 V	3.6 V
3.0 V	-2.5 V	3.0 V
2.7 V	-2.8 V	2.7 V
2.3 V	-3.2 V	2.3 V

8.4 Device Functional Modes

The function table for TS5A22362 is shown in Table 2

Table 2. Function Table

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
H	OFF	ON

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

Ensure that the device is powered up with a supply voltage on VCC before a voltage can be applied to the signal paths NC and NO.

Tie the digitally controlled inputs select pins IN1 and IN2 to VCC or GND to avoid unwanted switch states that could result if the logic control pins are left floating.

All unused digital inputs of the device must be held at VCC or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, [SCBA004](#).

9.2 Typical Application

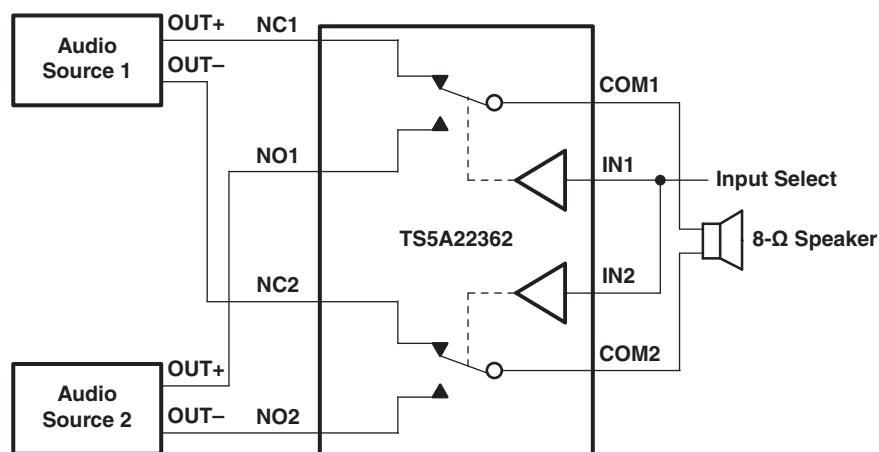


Figure 24. Typical Application

9.2.1 Design Requirements

Tie the digitally controlled inputs select pins IN1 and IN2 to VCC or GND to avoid unwanted switch states that could result if the logic control pins are left floating.

9.2.2 Detailed Design Procedure

Select the appropriate supply voltage to cover the entire voltage swing of the signal passing through the switch because the TS5A22362 operates from a single +2.3-V to +5.5-V supply and the input/output signal swing of the device is dependant of the supply voltage VCC. The device will pass signals as high as VCC and as low as VCC – 5.5 V. Use table 2 as a guide for selecting supply voltage based on the signal passing through the switch.

Ensure that the device is powered up with a supply voltage on VCC before a voltage can be applied to the signal paths NC and NO.

Typical Application (continued)

9.2.3 Application Curve

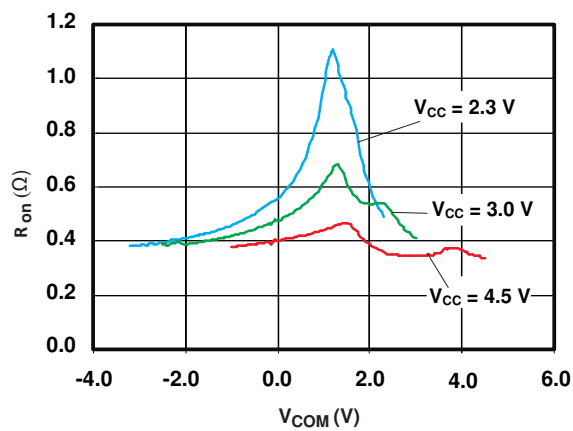


Figure 25. R_{on} vs V_{COM}

10 Power Supply Recommendations

The TS5A22362 operates from a single 2.3-V to 5.5-V supply. The device must be powered up with a supply voltage on VCC before a voltage can be applied to the signal paths NC and NO. It is recommended to include a 100- μ s delay after VCC is at voltage before applying a signal on NC and NO paths.

It is also good practice to place a 0.1- μ F bypass capacitor on the supply pin VCC to GND to smooth out lower frequency noise to provide better load regulation across the frequency spectrum.

11 Layout

11.1 Layout Guidelines

TI recommends placing a bypass capacitor as close to the supply pin VCC as possible to help smooth out lower frequency noise to provide better load regulation across the frequency spectrum.

Minimize trace lengths and vias on the signal paths in order to preserve signal integrity.

11.2 Layout Example

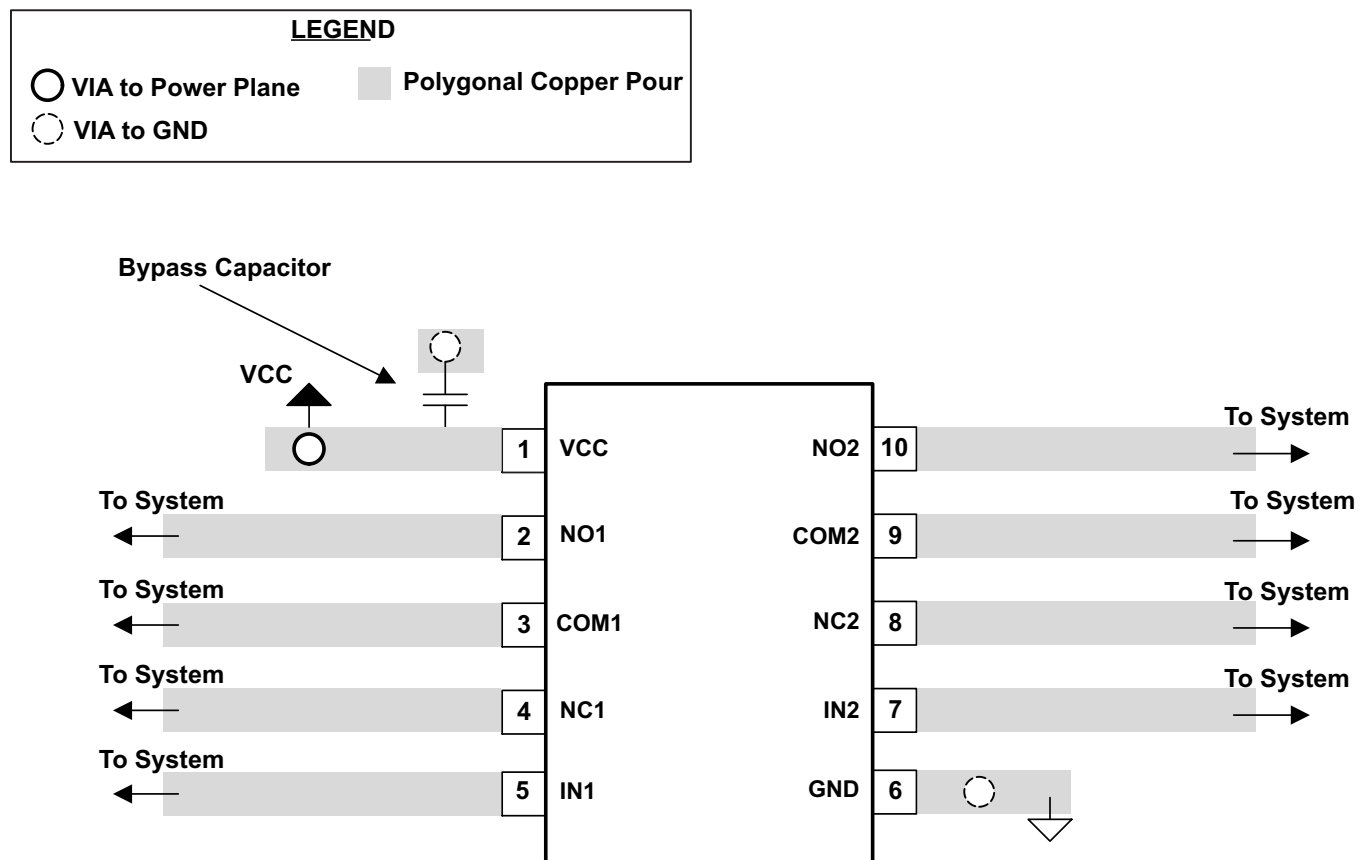


Figure 26. Layout example of TS5A22362

12 器件和文档支持

12.1 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。单击右上角的通知我进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

12.2 社区资源

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

12.3 商标

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.4 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

12.5 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TS5A22362DGSR	Active	Production	VSSOP (DGS) 10	2500 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	39R
TS5A22362DGSR.B	Active	Production	VSSOP (DGS) 10	2500 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 85	39R
TS5A22362DRCR	Active	Production	VSON (DRC) 10	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ZVG
TS5A22362DRCR.B	Active	Production	VSON (DRC) 10	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ZVG
TS5A22362DRCRG4	Active	Production	VSON (DRC) 10	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ZVG
TS5A22362DRCRG4.B	Active	Production	VSON (DRC) 10	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ZVG
TS5A22362YZPR	Active	Production	DSBGA (YZP) 10	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(39, 392)
TS5A22362YZPR.B	Active	Production	DSBGA (YZP) 10	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(39, 392)

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION



*All dimensions are nominal

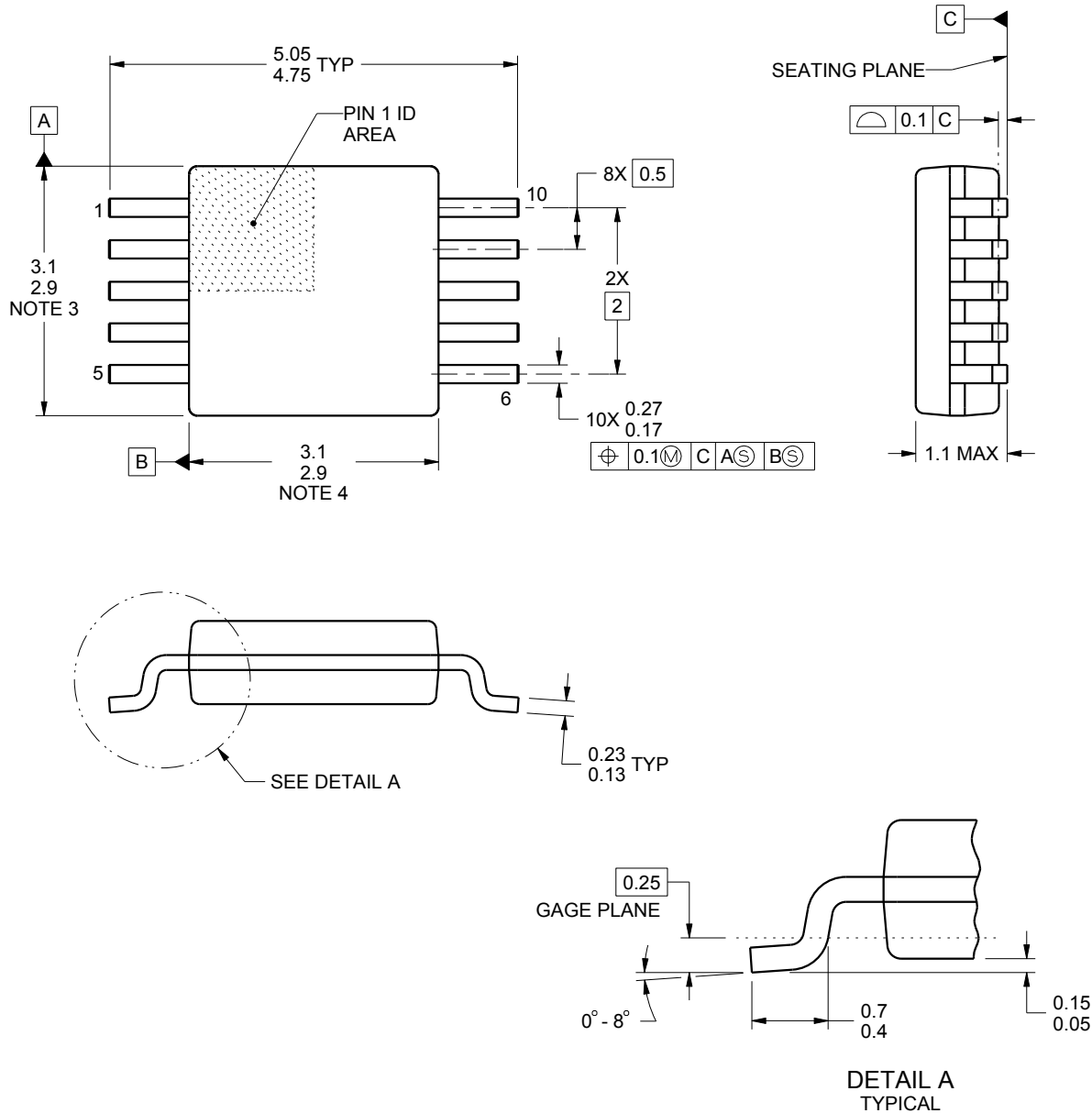
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A22362DGSR	VSSOP	DGS	10	2500	330.0	12.4	5.25	3.35	1.25	8.0	12.0	Q1
TS5A22362DGSR	VSSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TS5A22362DRCR	VSON	DRC	10	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TS5A22362DRCRG4	VSON	DRC	10	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TS5A22362YZPR	DSBGA	YZP	10	3000	178.0	9.2	1.49	1.99	0.63	4.0	8.0	Q2

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A22362DGSR	VSSOP	DGS	10	2500	366.0	364.0	50.0
TS5A22362DGSR	VSSOP	DGS	10	2500	358.0	335.0	35.0
TS5A22362DRCR	VSON	DRC	10	3000	353.0	353.0	32.0
TS5A22362DRCRG4	VSON	DRC	10	3000	353.0	353.0	32.0
TS5A22362YZPR	DSBGA	YZP	10	3000	220.0	220.0	35.0



4221984/A 05/2015

NOTES:

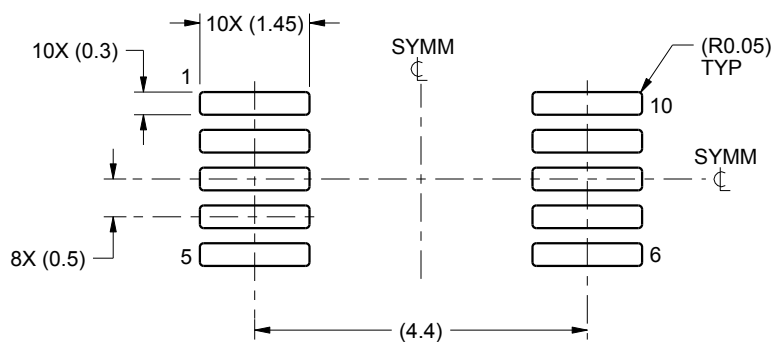
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187, variation BA.

EXAMPLE BOARD LAYOUT

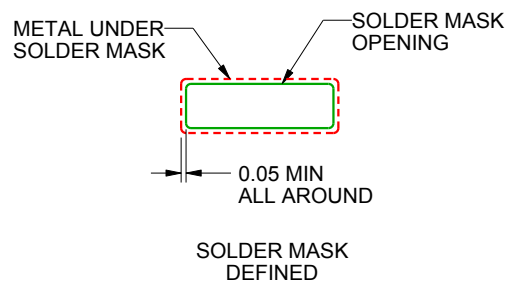
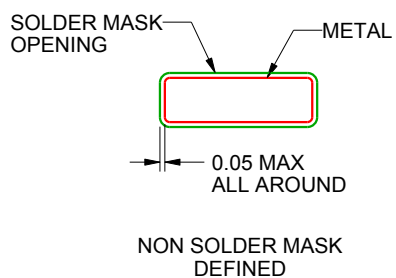
DGS0010A

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
SCALE:10X



SOLDER MASK DETAILS
NOT TO SCALE

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NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

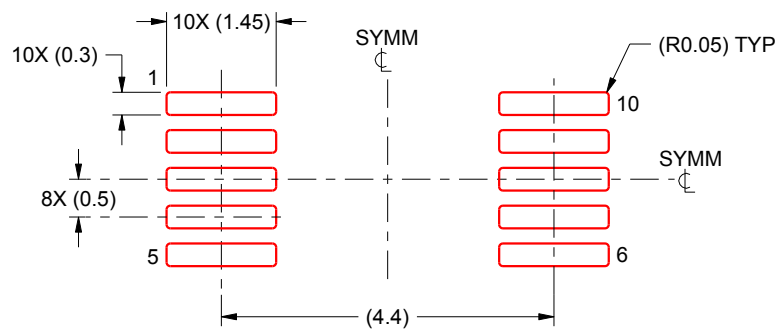
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DGS0010A

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:10X

4221984/A 05/2015

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

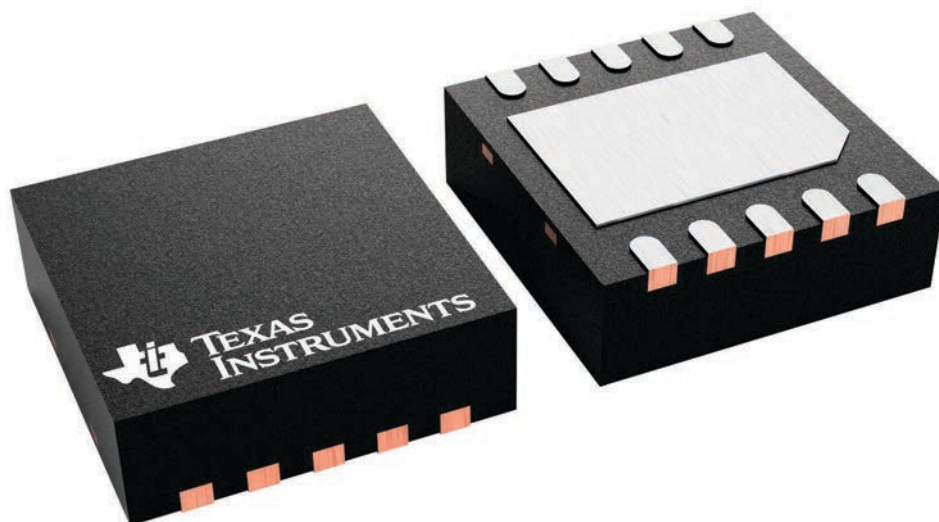
DRC 10

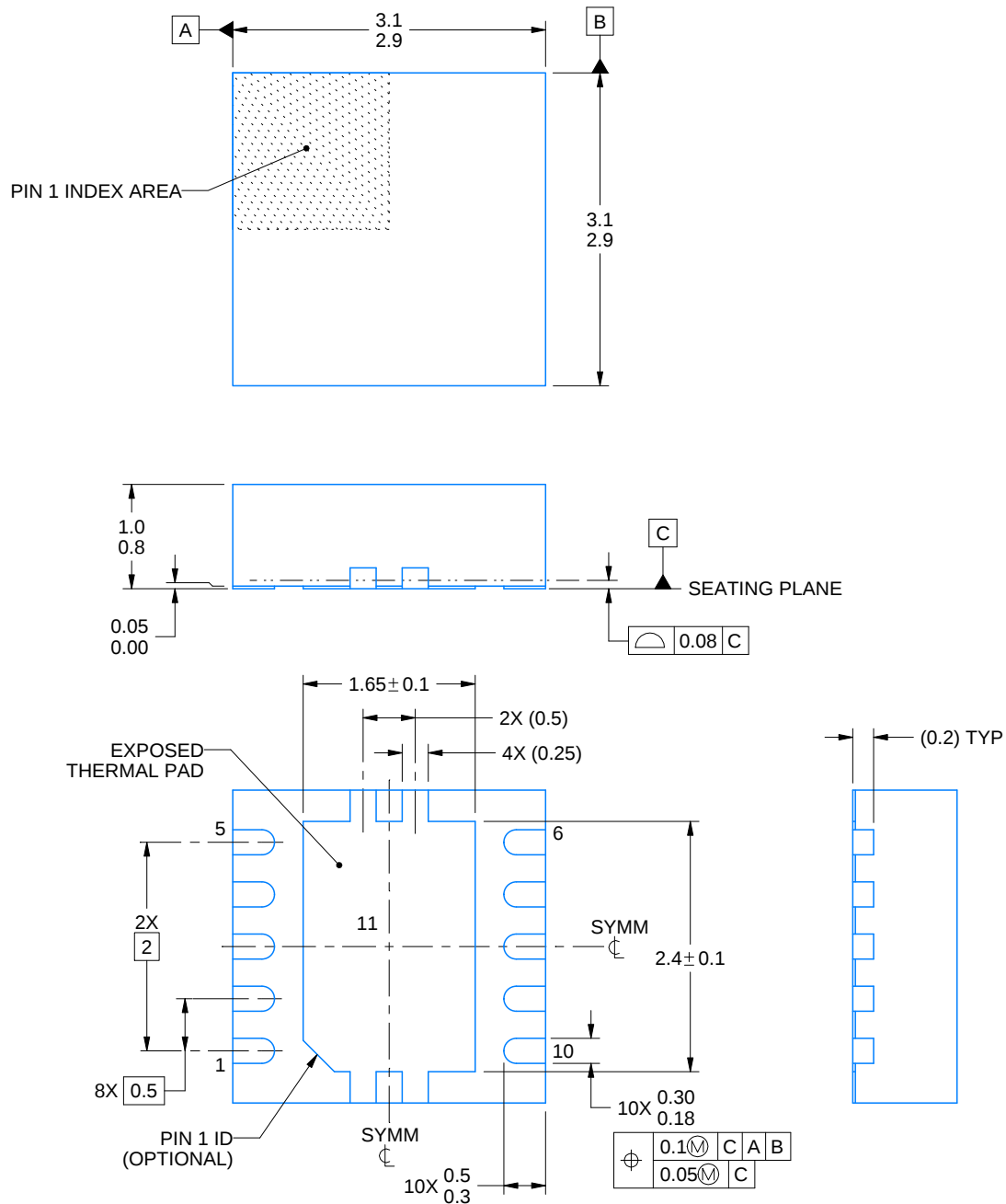
VSON - 1 mm max height

3 x 3, 0.5 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.





4218878/B 07/2018

NOTES:

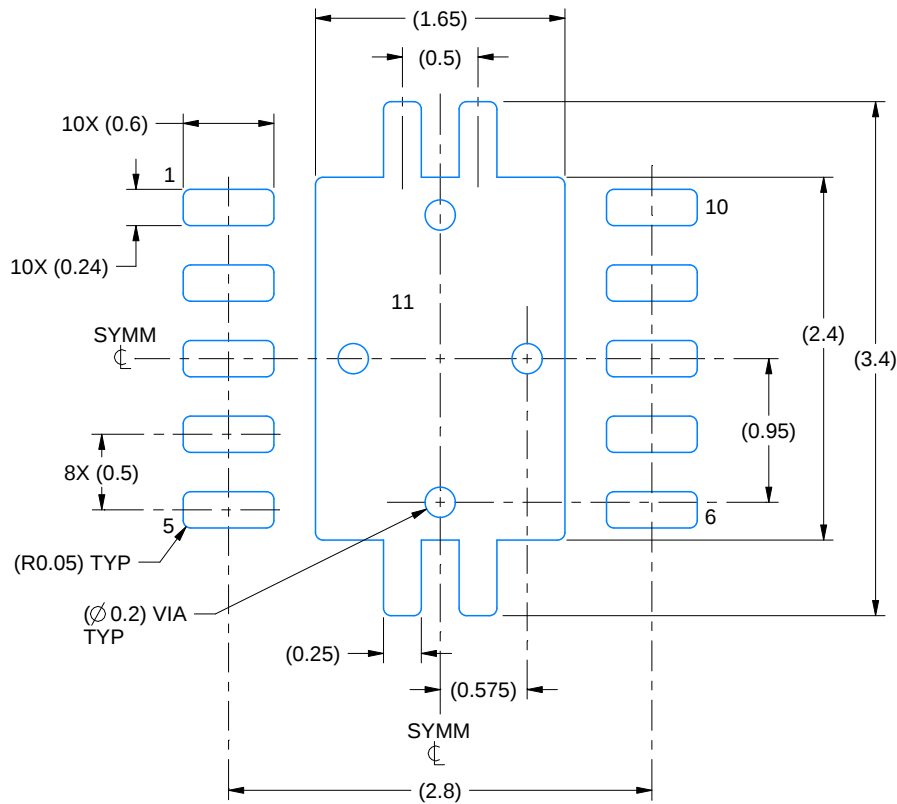
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.

EXAMPLE BOARD LAYOUT

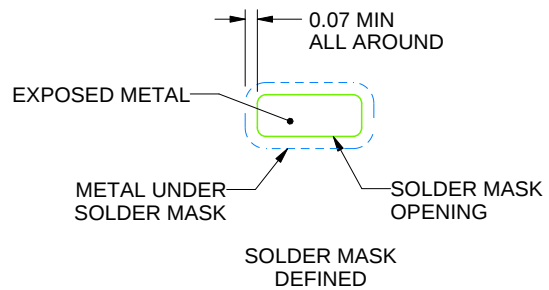
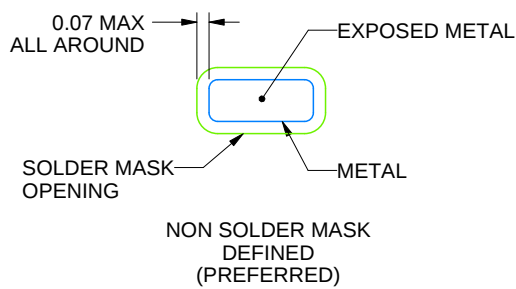
DRC0010J

VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:20X



SOLDER MASK DETAILS

4218878/B 07/2018

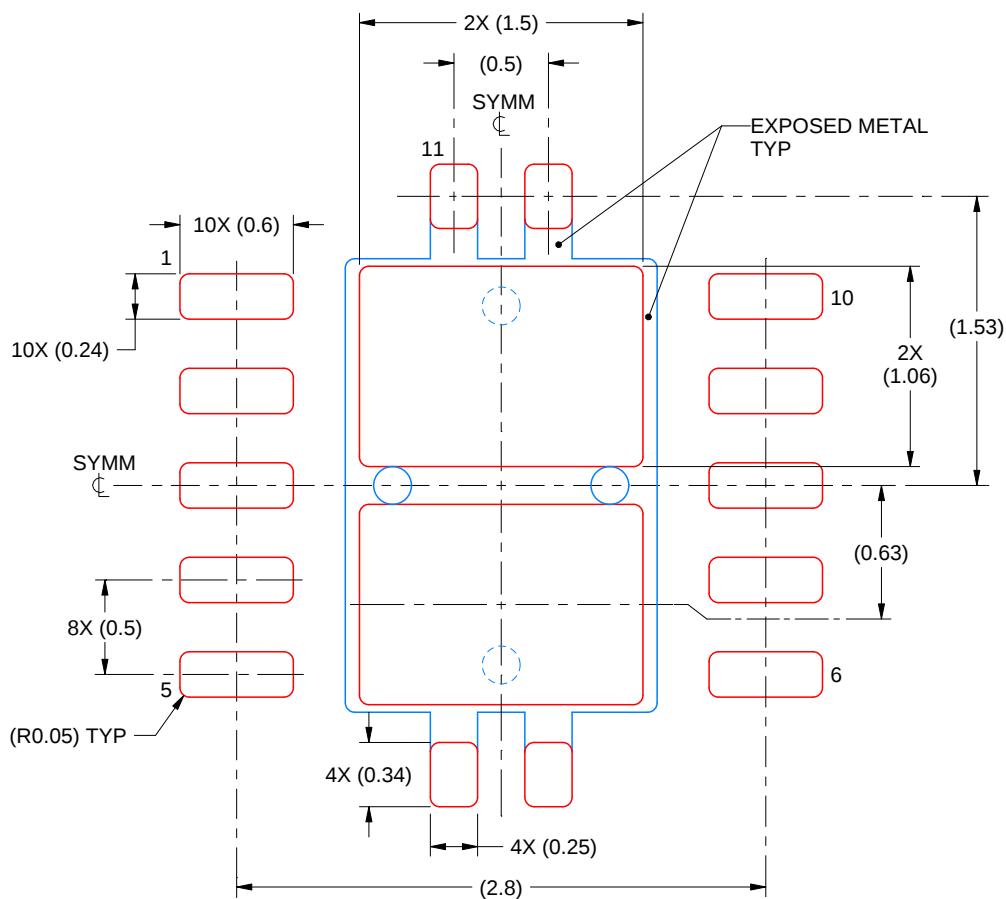
NOTES: (continued)

- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

DRC0010J

VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



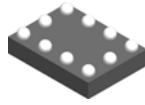
SOLDER PASTE EXAMPLE BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 11:
80% PRINTED SOLDER COVERAGE BY AREA
SCALE:25X

4218878/B 07/2018

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

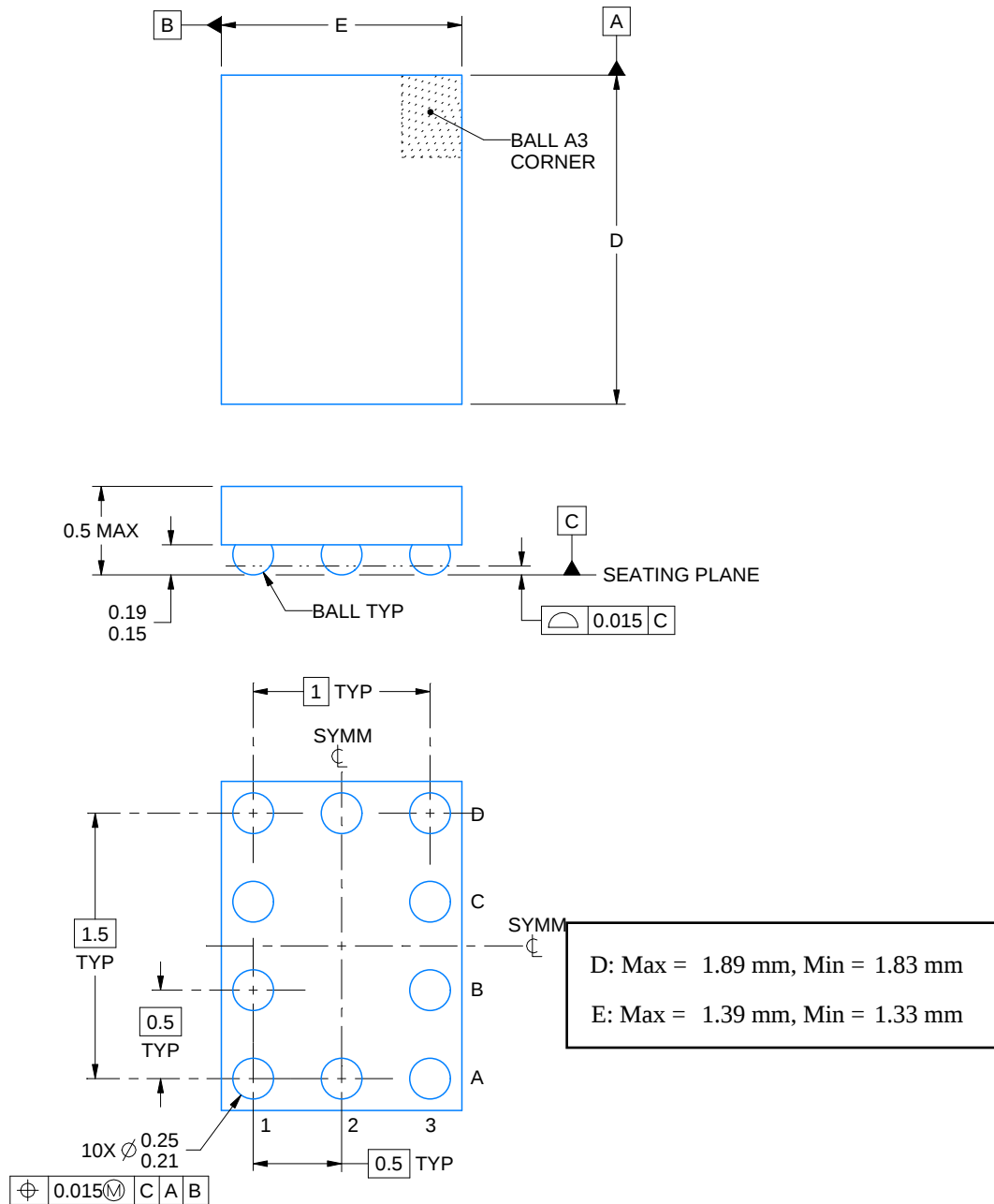


YZP0010

PACKAGE OUTLINE

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



4219350/B 11/2017

NOTES:

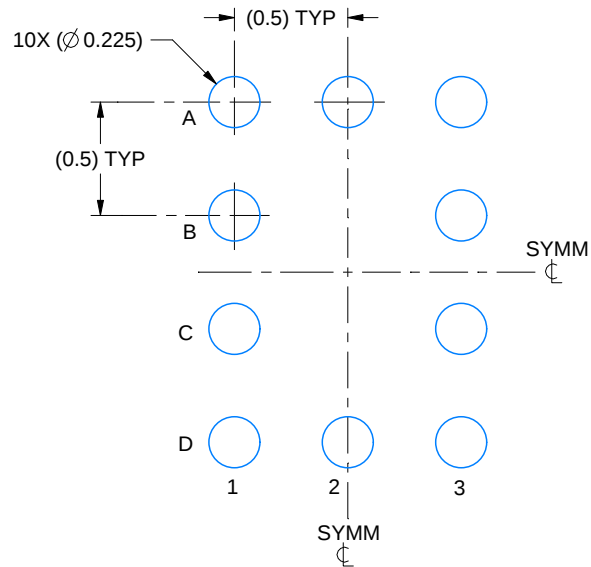
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

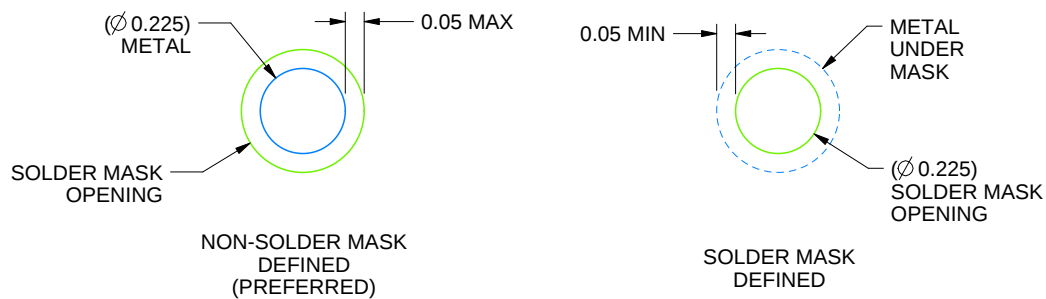
YZP0010

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



LAND PATTERN EXAMPLE
SCALE:30X



SOLDER MASK DETAILS
NOT TO SCALE

4219350/B 11/2017

NOTES: (continued)

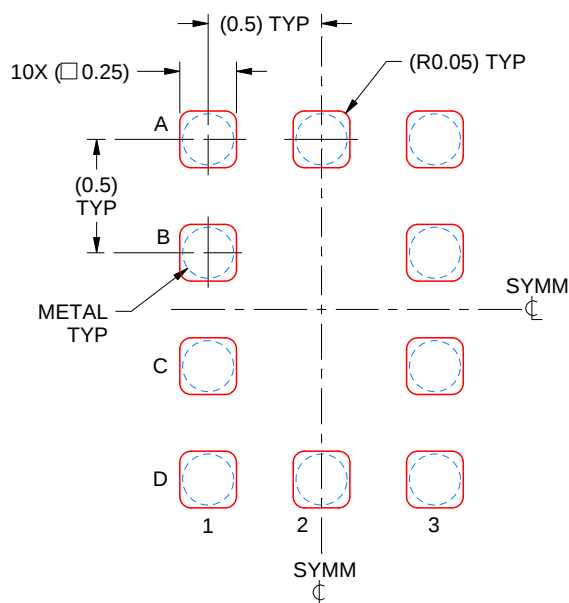
- Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).

EXAMPLE STENCIL DESIGN

YZP0010

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:30X

4219350/B 11/2017

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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